



# **FQPF4N90C Information**



For Reference Only

Part Number FQPF4N90C

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 900V 4A TO-220F

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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# **FQPF4N90C Specifications**

Manufacturer Part Number         FQPF4N90C           Manufacturer         Fairchild/ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3 Full Pack           Series         QFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         900V           Current - Continuous Drain (Id) @ 25°C         4A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         22nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         960pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         47W (Tc)           Rds On (Max) @ Id, Vgs         4.2 Ohm @ 2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220F           Package / Case         TO-2203 Full Pack		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3 Full Pack           Series         QFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         900V           Current - Continuous Drain (Id) @ 25°C         4A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         22nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         960pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         47W (Tc)           Rds On (Max) @ Id, Vgs         4.2 Ohm @ 2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220F           Package / Case         TO-220-3 Full Pack	Manufacturer Part Number	FQPF4N90C
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)900VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs22nC @ 10VInput Capacitance (Ciss) (Max) @ Vds960pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)47W (Tc)Rds On (Max) @ Id, Vgs4.2 Ohm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPackage / CaseTO-220-3 Full Pack	Package	TO-220-3 Full Pack
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Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  St @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.2 Ohm @ 2A, 10V  Operating Temperature  Supplier Device Package  Package / Case  TO-220F  Package / Case	Drain to Source Voltage (Vdss)	900V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  960pF @ 25V  Vgs (Max)  ±30V  FET Feature  - Power Dissipation (Max)  A7W (Tc)  Rds On (Max) @ Id, Vgs  4.2 Ohm @ 2A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220F  Package / Case  TO-220-3 Full Pack	Current - Continuous Drain (Id) @ 25°C	4A (Tc)
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Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220F  Package / Case  TO-220-3 Full Pack	Power Dissipation (Max)	47W (Tc)
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Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220F
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

### **FQPF4N90C Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **FQPF4N90C Payment Methods**



















## **FQPF4N90C Shipping Methods**













If you have any question about FQPF4N90C, please do not hesitate to contact us!

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